

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SC5386

HORIZONTAL DEFLECTION OUTPUT FOR HIGH RESOLUTION DISPLAY, COLOR TV

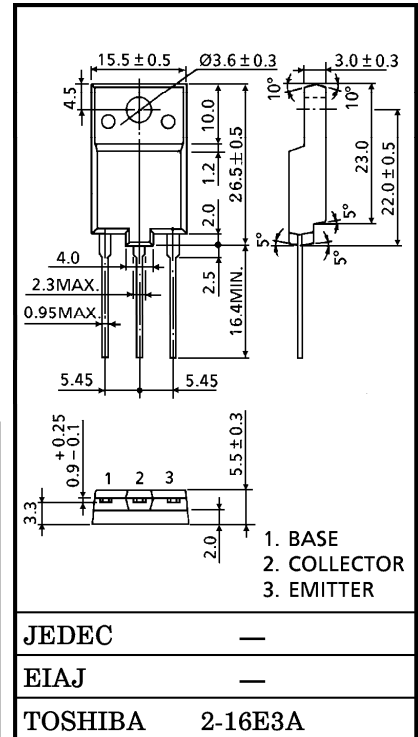
HIGH SPEED SWITCHING APPLICATIONS

- High Voltage : $V_{CB0} = 1500\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 3\text{ V (Max.)}$
- High Speed : $t_f = 0.15\ \mu\text{s (Typ.)}$
- Collector Metal (Fin) is Fully Covered with Mold Resin.

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

| CHARACTERISTIC | | SYMBOL | RATING | UNIT |
|--|-------|-----------|---------|------------------|
| Collector-Base Voltage | | V_{CB0} | 1500 | V |
| Collector-Emitter Voltage | | V_{CEO} | 600 | V |
| Emitter-Base Voltage | | V_{EBO} | 5 | V |
| Collector Current | DC | I_C | 8 | A |
| | Pulse | I_{CP} | 16 | |
| Base Current | | I_B | 4 | A |
| Collector Power Dissipation ($T_c = 25^\circ\text{C}$) | | P_C | 50 | W |
| Junction Temperature | | T_j | 150 | $^\circ\text{C}$ |
| Storage Temperature Range | | T_{stg} | -55~150 | $^\circ\text{C}$ |

Unit in mm



Weight : 5.5 g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|--------------------------------------|--------------|---------------|---|------|------|------|---------------|
| Collector Cut-off Current | | I_{CBO} | $V_{CB} = 1500\text{ V}, I_E = 0$ | — | — | 1 | mA |
| Emitter Cut-off Current | | I_{EBO} | $V_{EB} = 5\text{ V}, I_C = 0$ | — | — | 10 | μA |
| Emitter-Base Breakdown Voltage | | $V_{(BR)CEO}$ | $I_C = 10\text{ mA}, I_B = 0$ | 600 | — | — | V |
| DC Current Gain | | $h_{FE(1)}$ | $V_{CE} = 5\text{ V}, I_C = 1\text{ A}$ | 15 | — | 35 | |
| | | $h_{FE(2)}$ | $V_{CE} = 5\text{ V}, I_C = 6\text{ A}$ | 4.3 | — | 7.5 | |
| Collector-Emitter Saturation Voltage | | $V_{CE(sat)}$ | $I_C = 6\text{ A}, I_B = 1.5\text{ A}$ | — | — | 3 | V |
| Base-Emitter Saturation Voltage | | $V_{BE(sat)}$ | $I_C = 6\text{ A}, I_B = 1.5\text{ A}$ | — | 1.0 | 1.5 | V |
| Transition Frequency | | f_T | $V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$ | — | 1.7 | — | MHz |
| Collector Output Capacitance | | C_{ob} | $V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$ | — | 105 | — | pF |
| Switching Time | Storage Time | t_{stg} | $I_{CP} = 5\text{ A}, I_{B1}(\text{end}) = 1.0\text{ A}$ $f_H = 64\text{ kHz}$ | — | 2.5 | 3.5 | μs |
| | Fall Time | t_f | | — | 0.15 | 0.3 | |

